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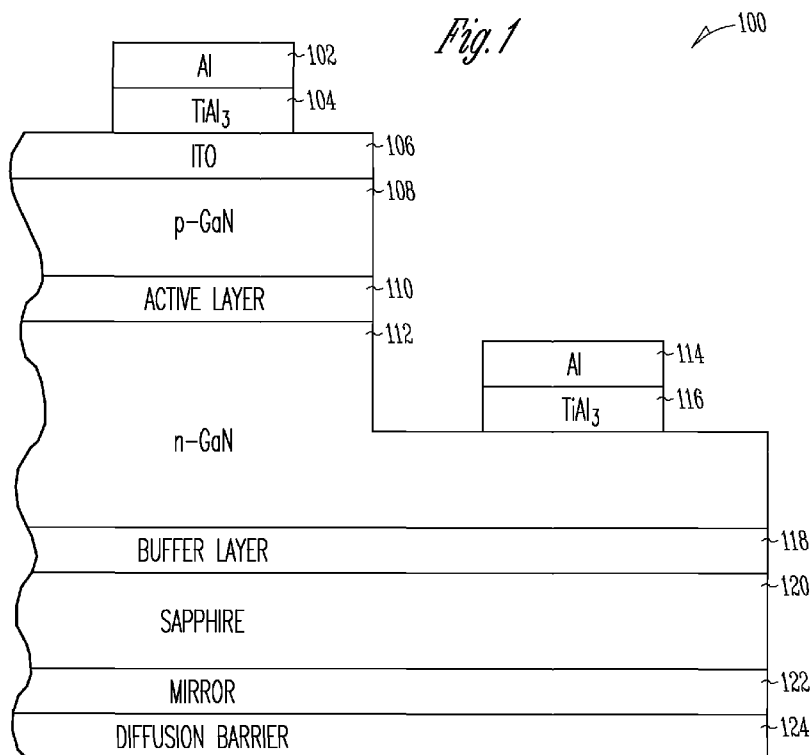
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(54) Title: OHMIC CONTACTS FOR SEMICONDUCTOR STRUCTURES



(57) Abstract: A composition and method for formation of ohmic contacts on a semiconductor structure are provided. The composition includes a TiAl_xN_y material at least partially contiguous with the semiconductor structure. The TiAl_xN_y material can be TiAl_3 . The composition can include an aluminum material, the aluminum material being contiguous to at least part of the TiAl_xN_y material, such that the TiAl_xN_y material is between the aluminum material and the semiconductor structure. The method includes annealing the composition to form an ohmic contact on the semiconductor structure.

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